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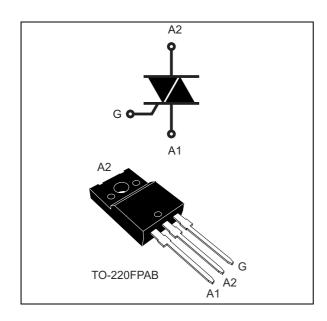






6 A logic level Triac

Datasheet - production data



Description

Available in through-hole fullpack package, the T610T-8FP Triac can be used for the on/off or phase angle control function in general purpose AC switching. This device can be directly driven by a microcontroller thanks to its 10 mA gate current requirement. Provide UL certified insulation rated at 2000 VRMS.

Table 1. Device summary

Symbol	Value	Unit
I _{T(rms)}	6	Α
V_{DRM}, V_{RRM}	800	V
V _{DSM} , V _{RSM}	900	V
I _{GT}	10	mA

Features

- Medium current Triac
- Three triggering quadrants Triac
- ECOPACK®2 compliant component
- Complies with UL standards (File ref: E81734)
- 6 A high performance Triac:
 - High T_i family
 - High dl/dt family
 - High dV/dt family
- Insulated package TO-220FPAB:
 - Insulated voltage: 2000 VRMS

Applications

- · General purpose AC line load switching
- · Motor control circuits
- Small home appliances
- Lighting
- Inrush current limiting circuits
- Overvoltage crowbar protection

Characteristics T610T-8FP

1 Characteristics

Table 2. Absolute maximum ratings ($T_i = 25$ °C unless otherwise stated)

Symbol	Paramete	Value	Unit		
I _{T(rms)}	On-state rms current (full sine wave)	T _c = 117 °C	6	Α
l	Non repetitive surge peak on-state	F = 50 Hz	t = 20 ms	45	Α
I _{TSM}	current (full cycle, T _j initial = 25 °C)	F = 60 Hz	t = 16.7 ms	47	^
l ² t	I^2 t value for fusing, T_j initial = 25 °C		t _p = 10 ms	13	A ² s
V _{DRM} ,	Popotitivo curgo poak off stato volta	90	T _j = 150 °C	600	V
V_{RRM}	nepetitive surge peak oil-state voita	Repetitive surge peak off-state voltage		800	V
V _{DSM} , V _{RSM}	Non repetitive surge peak off-state v	repetitive surge peak off-state voltage		900	V
dI/dt	Critical rate of rise of on-state current $I_G = 2 \times I_{GT}$, $t_r \le 100 \text{ ns}$	1 L = 100 Hz		100	A/μs
I_{GM}	Peak gate current	t _p = 20 μs	T _j = 150 °C	4	Α
P _{G(AV)}	Average gate power dissipation		T _j = 150 °C	1	W
T _{stg} T _j	Storage junction temperature range Operating junction temperature range		- 40 to + 150 - 40 to + 150	°C	
T _L	Maximum lead temperature for soldering during 10 s		260	°C	
V _{ins}	Insulation rms voltage, 1 minute			2	kV

Table 3. Electrical characteristics (T $_{\rm j}$ = 25 °C, unless otherwise stated)

Symbol	Test conditions	Quadrant		Value	Unit
	V 10 V B 20 O	1 - 11 - 111	Min.	0.5	mA
I _{GT}	$V_D = 12 \text{ V}, R_L = 30 \Omega$	1 - 11 - 111	Max.	10	
V _{GT}	$V_D = 12 \text{ V}, R_L = 30 \Omega$	1 - 11 - 111	Max.	1.3	V
V _{GD}	$V_D = V_{DRM}, R_L = 3.3 \text{ k} \Omega, T_j = 150 \text{ °C}$	1 - 11 - 111	Min.	0.2	V
I _H ⁽¹⁾	I _T = 500 mA		Max.	15	mA
1	1.121	1 - 111	Max.	20	mA
IL	$I_{G} = 1.2 I_{GT}$	II	Max.	25	mA
dV/dt ⁽¹⁾	$V_D = V_R = 536 \text{ V}, \text{ gate open}$	T _j = 125 °C	Min.	250	V/µs
u v/ut · /	V _D = V _R = 402 V, gate open	T _j = 150 °C	IVIII I.	170	V/µs
(dl/dt)c (1)	(a) (/a) (a) (a) (a) (a) (a) (a) (a) (a) (a) (T _j = 125 °C	Min.	5.2	A/ms
(ui/ut)c ·	$(dV/dt)c = 0.1 V/\mu s$	T _j = 150 °C	IVIII I.	3.7	A/IIIS
(dl/dt)c (1)	$(dV/dt)c = 10 V/\mu s$	T _j = 125 °C	Min.	2.7	A/ms
(di/dt)C (1)		T _j = 150 °C	IVIII I.	1.2	

^{1.} For both polarities of A2 referenced to A1

T610T-8FP Characteristics

Table	1	Statio	characteristics	
Table	4.	Sianc	cnaracteristics	š

Symbol	Test conditions			Value	Unit
V _T ⁽¹⁾	$I_{TM} = 8.5 \text{ A}, t_p = 380 \ \mu \text{s}$	T _j = 25 °C	Max.	1.55	V
V _{t0} (1)	Threshold voltage	T _j = 150 °C	Max.	0.85	V
R _d ⁽¹⁾	Dynamic resistance	T _j = 150 °C	Max.	75	mΩ
	V _{DRM} = V _{RRM} = 800 V	T _j = 25 °C	Max.	5	μΑ
I _{DRM}	VDRM = VRRM = 800 V	T _j = 125 °C	iviax.	0.6	mA
IRRM	V _{DRM} = V _{RRM} = 600 V	T _j = 150 °C	Max.	2.0	IIIA

^{1.} For both polarities of A2 referenced to A1

Table 5. Thermal resistance

Symbol	Parameter	Value	Unit
R _{th(j-c)}	Junction to case (AC)	4.5	°C/W
R _{th(j-a)}	Junction to ambient (DC)	60	°C/W

Figure 1. Maximum power dissipation versus on-state rms current (full cycle)

8 P(W)
6 4 2 180 17(RMS)(A) 180° 0 1 2 3 4 5 6

Figure 2. On-state rms current versus case temperature (full cycle)

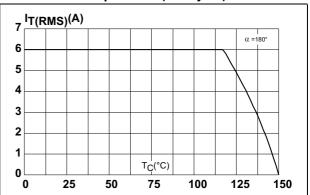


Figure 3. On-state rms current versus ambient temperature (free air convection)

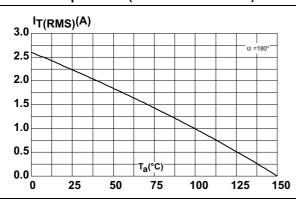
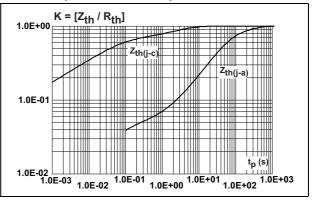


Figure 4. Relative variation of thermal impedance versus pulse duration



Characteristics T610T-8FP

Figure 5. On-state characteristics (maximum values)

100 I_{TM}(A)

100 T_{I,max}:

V_{i,=0.85}V
R_{i,=75} mΩ

V_{TM}(V)

10.0 0.5 1.0 1.5 2.0 2.5 3.0 3.5 4.0

Figure 6. Surge peak on-state current versus number of cycles

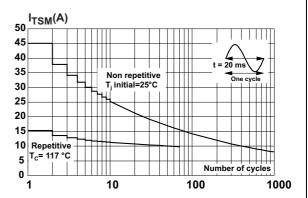


Figure 7. Non repetitive surge peak on-state current and corresponding values of I²t

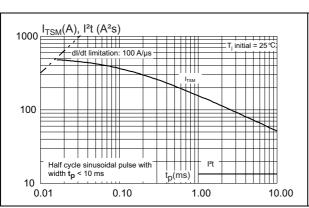


Figure 8. Relative variation of gate trigger current and gate voltage versus junction temperature (typical values)

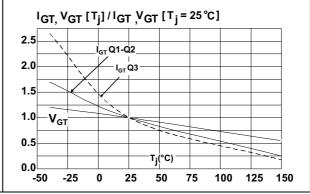


Figure 9. Relative variation of static dV/dt immunity versus junction temperature (typical values)

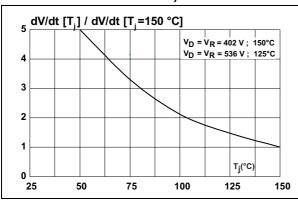
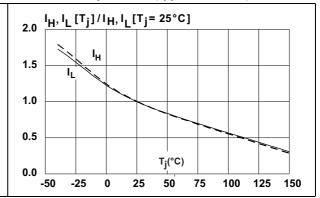


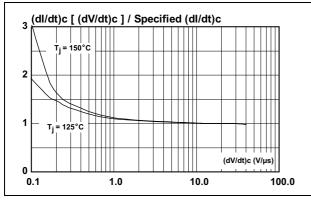
Figure 10. Relative variation of holding current and latching current versus junction temperature (typical values)



T610T-8FP Characteristics

Figure 11. Relative variation of critical rate of decrease of main current (dl/dt)c versus reapplied (dV/dt)c (typical values)

Figure 12. Relative variation of critical rate of decrease of main current (dl/dt)c versus junction temperature (typical values)



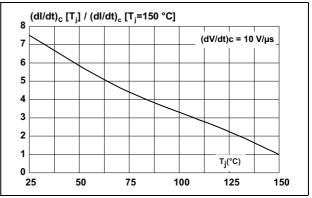
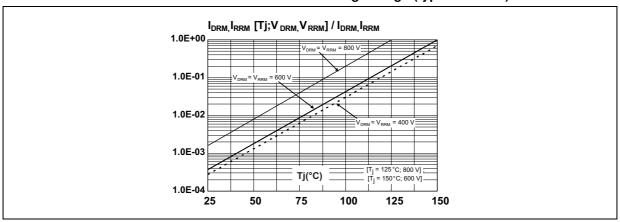


Figure 13. Relative variation of leakage current versus junction temperature for different values of blocking voltage (typical values)



Package information T610T-8FP

2 Package information

- Epoxy meets UL94, V0
- Lead-free package
- Recommended torque: 0.4 to 0.6 N·m

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: *www.st.com*. ECOPACK[®] is an ST trademark.

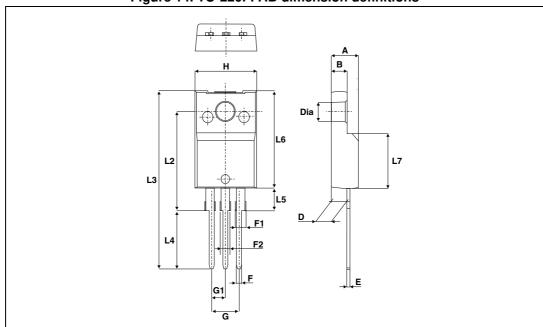


Figure 14. TO-220FPAB dimension definitions

T610T-8FP Package information

Table 6. TO-220FPAB dimensions

	Dimensions				
Ref.	Millin	neters	Inc	hes	
	Min.	Max.	Min.	Max.	
А	4.4	4.6	0.173	0.181	
В	2.5	2.7	0.098	0.106	
D	2.5	2.75	0.098	0.108	
Е	0.45	0.70	0.018	0.027	
F	0.75	1	0.030	0.039	
F1	1.15	1.70	0.045	0.067	
F2	1.15	1.70	0.045	0.067	
G	4.95	5.20	0.195	0.205	
G1	2.4	2.7	0.094	0.106	
Н	10	10.4	0.393	0.409	
L2	16 ⁻	Тур.	0.63	Тур.	
L3	28.6	30.6	1.126	1.205	
L4	9.8	10.6	0.386	0.417	
L5	2.9	3.6	0.114	0.142	
L6	15.9	16.4	0.626	0.646	
L7	9.00	9.30	0.354	0.366	
Dia.	3.00	3.20	0.118	0.126	

Ordering information T610T-8FP

3 Ordering information

Figure 15. Ordering information scheme

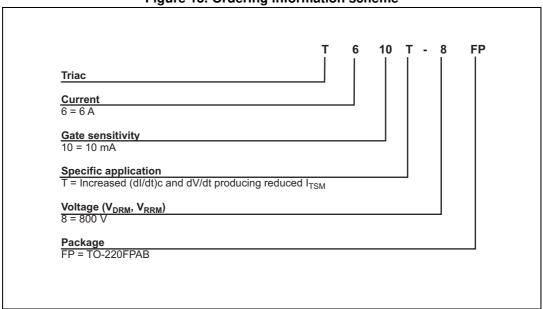


Table 7. Ordering information

Order code	Marking	Package	Weight	Base qty	Delivery mode
T610T-8FP	T610T-8FP	TO-220FPAB	2.0 g	50	Tube

4 Revision history

Table 8. Document revision history

Date	Revision	Changes
05-Feb-2014	1	Initial release.
12-Feb-2015	2	Updated Features and Table 2.

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